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PE43713

Product Specification

UltraCMOS® RF Digital Step Attenuator, 9 kHz–6 GHz

Features

- Flexible attenuation steps of 0.25 dB, 0.5 dB and 1 dB up to 31.75 dB
- Glitch-less attenuation state transitions
- Monotonicity: 0.25 dB up to 4 GHz, 0.5 dB up to 5 GHz and 1 dB up to 6 GHz
- Extended +105 °C operating temperature
- Parallel and Serial programming interfaces with Serial Addressability
- Packaging—32-lead 5 × 5 mm QFN

Applications

- Test and measurement (T&M)
- General purpose RF attenuator
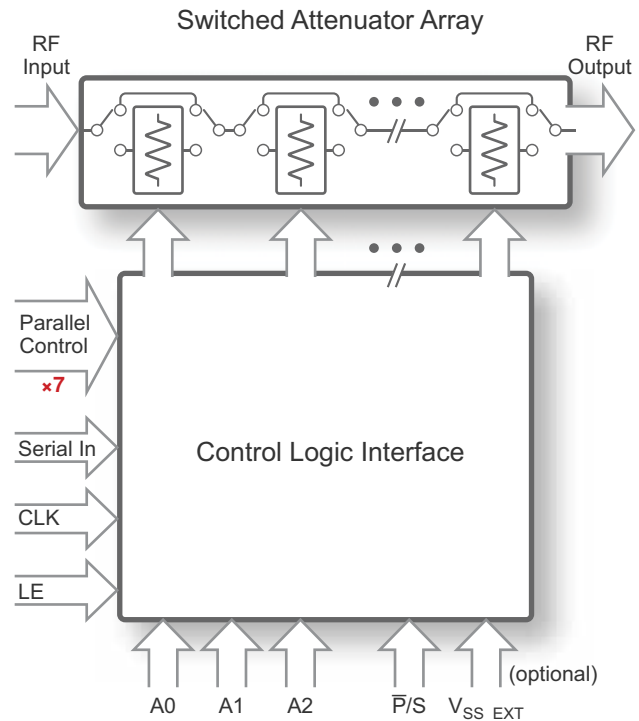
Product Description

The PE43713 is a 50Ω, HaRP™ technology-enhanced, 7-bit RF digital step attenuator (DSA) that supports a broad frequency range from 9 kHz to 6 GHz. It features glitch-less attenuation state transitions, supports 1.8V control voltage and includes an extended operating temperature range to +105 °C and optional V_{SS_EXT} bypass mode to improve spurious performance, making this device ideal for test and measurement (T&M).

The PE43713 is a pin-compatible upgraded version of the PE43703. An integrated digital control interface supports both Serial Addressable and Parallel programming of the attenuation, including the capability to program an initial attenuation state at power-up.

The PE43713 covers a 31.75 dB attenuation range in 0.25 dB, 0.5 dB and 1dB steps. It is capable of maintaining 0.25 dB monotonicity through 4 GHz, 0.50 dB monotonicity through 5 GHz and 1 dB monotonicity through 6 GHz. In addition, no external blocking capacitors are required if 0 VDC is present on the RF ports.

The PE43713 is manufactured on Peregrine's UltraCMOS® process, a patented variation of silicon-on-insulator (SOI) technology on a sapphire substrate.

ULTRACMOS®
www.psemi.com

Peregrine's HaRP technology enhancements deliver high linearity and excellent harmonics performance. It is an innovative feature of the UltraCMOS process, offering the performance of GaAs with the economy and integration of conventional CMOS.

Optional External V_{SS} Control

For proper operation, the V_{SS_EXT} control pin must be grounded or tied to the V_{SS} voltage specified in **Table 2**. When the V_{SS_EXT} control pin is grounded, FETs in the switch are biased with an internal negative voltage generator. For applications that require the lowest possible spur performance, V_{SS_EXT} can be applied externally to bypass the internal negative voltage generator.

Absolute Maximum Ratings

Exceeding absolute maximum ratings listed in **Table 1** may cause permanent damage. Operation should be restricted to the limits in **Table 2**. Operation between operating range maximum and absolute maximum for extended periods may reduce reliability.

ESD Precautions

When handling this UltraCMOS device, observe the same precautions as with any other ESD-sensitive devices. Although this device contains circuitry to protect it from damage due to ESD, precautions should be taken to avoid exceeding the rating specified in **Table 1**.

Latch-up Immunity

Unlike conventional CMOS devices, UltraCMOS devices are immune to latch-up.

Table 1 • *Absolute Maximum Ratings for PE43713*

Parameter/Condition	Min	Max	Unit
Supply voltage, V_{DD}	−0.3	5.5	V
Digital input voltage	−0.3	3.6	V

RF input power, 50Ω
    9 kHz–48 MHz
    >48 MHz–6 GHz
		Figure 5
		+31
			dBm
			dBm

Storage temperature range	−65	+150	°C
ESD voltage HBM, all pins[1]		3000	V
ESD voltage CDM, all pins[2]		1000	V

Notes:
  1) Human body model (MIL–STD 883 Method 3015).
  2) Charged device model (JEDEC JESD22–C101).			

Recommended Operating Conditions

Table 2 lists the recommending operating condition for the PE43713. Devices should not be operated outside the recommended operating conditions listed below.

Table 2 • *Recommended Operating Condition for PE43713*

Parameter	Min	Typ	Max	Unit
Normal mode, V_{SS_EXT} = 0V[1]				
Supply voltage, V_{DD}	2.3		5.5	V
Supply current, I_{DD}		150	200	µA
Bypass mode, V_{SS_EXT} = –3.4V[2]				
Supply voltage, V_{DD} (V_{DD} ≥ 3.4V see **Table 3** for full spec compliance)	2.7	3.4	5.5	V
Supply current, I_{DD}		50	80	µA
Negative supply voltage, V_{SS_EXT}	–3.6		–2.4	V
Negative supply current, I_{SS}	–40	–16		µA
Normal or bypass mode				
Digital input high	1.17		3.6	V
Digital input low	–0.3		0.6	V
Digital input current			17.5	µA

RF input power, CW[3]
    9 kHz–48 MHz
    >48 MHz–6 GHz
			Figure 5
			+23
				dBm
				dBm

RF input power, pulsed[4]
    9 kHz–48 MHz
    >48 MHz–6 GHz
			Figure 5
			+28
				dBm
				dBm

Operating temperature range	–40	+25	+105	°C

Notes:
  1) Normal mode: connect V_{SS_EXT} (pin 20) to GND (V_{SS_EXT} = 0V) to enable internal negative voltage generator.
  2) Bypass mode: use V_{SS_EXT} (pin 20) to bypass and disable internal negative voltage generator.
  3) 100% duty cycle, all bands, 50Ω.
  4) Pulsed, 5% duty cycle of 4620 µs period, 50Ω.				

Electrical Specifications

Table 3 provides the PE43713 key electrical specifications at 25 °C, RF1 = RF_{IN}, RF2 = RF_{OUT} ($Z_S = Z_L = 50\Omega$), unless otherwise specified. Normal mode[1] is at V_{DD} = 3.3V and V_{SS_EXT} = 0V. Bypass mode[2] is at V_{DD} = 3.4V and V_{SS_EXT} = −3.4V.

Table 3 • *PE43713 Electrical Specifications*

Parameter	Condition	Frequency	Min	Typ	Max	Unit
Operating frequency			9 kHz		6 GHz	As shown
Attenuation range	0.25 dB step 0.5 dB step 1 dB step			0–31.75 0–31.50 0–31.00		dB dB dB
Insertion loss		9 kHz–1.0 GHz 1.0–2.2 GHz 2.2–4.0 GHz 4.0–6.0 GHz		1.3 1.6 1.95 2.45	1.5 1.85 2.4 2.8	dB dB dB dB
Attenuation error	**0.25 dB step**					
	0–8 dB	9 kHz–2.2 GHz			±(0.20 + 1.5% of attenuation setting)	dB
	8.25–31.75 dB	9 kHz–2.2 GHz			±(0.20 + 2.0% of attenuation setting)	dB
	0–31.75 dB	>2.2–3.0 GHz			±(0.15 + 3.0% of attenuation setting)	dB
	0–31.75 dB	>3.0–4.0 GHz			±(0.25 + 3.5% of attenuation setting)	dB
	0.5 dB step					
	0–8 dB	9 kHz–2.2 GHz			±(0.20 + 1.5% of attenuation setting)	dB
	8.5–31.5 dB	9 kHz–2.2 GHz			±(0.20 + 2.0% of attenuation setting)	dB
	0–31.5 dB	>2.2–3.0 GHz			±(0.15 + 3.0% of attenuation setting)	dB
	0–31.5 dB	>3.0–5.0 GHz			±(0.25 + 5.0% of attenuation setting)	dB

Table 3 • PE43713 Electrical Specifications (Cont.)

Parameter	Condition	Frequency	Min	Typ	Max	Unit
Attenuation error	**1 dB step**					
	0–8 dB	9 kHz–2.2 GHz			±(0.20 + 1.5% of attenuation setting)	dB
	9–31 dB	9 kHz–2.2 GHz			±(0.20 + 2.0% of attenuation setting)	dB
	0–31 dB	>2.2–3.0 GHz			±(0.15 + 3.0% of attenuation setting)	dB
	0–31 dB	>3.0–5.0 GHz			±(0.25 + 5.0% of attenuation setting)	dB
	0–31 dB	>5.0–6.0 GHz			±(0.25 + 5.0% of attenuation setting)	dB
Return loss	Input port or output port	9 kHz–4 GHz 4–6 GHz		13 15		dB dB
Relative phase	All states	9 kHz–4 GHz 4–6 GHz		27 42		deg deg
Input 0.1dB compression point[3]		48 MHz–6 GHz		31		dBm
Input IP3	Two tones at +18 dBm, 20 MHz spacing	4 GHz 6 GHz		57 56		dBm dBm
RF T$_{rise}$/T$_{fall}$	10%/90% RF			200		ns
Settling time	RF settled to within 0.05 dB of final value			1.6		µs
Switching time	50% CTRL to 90% or 10% RF			275		ns
Attenuation transient (envelope)		2 GHz		0.3		dB

Notes:

1) Normal mode: connect V$_{SS\_EXT}$ (pin 20) to GND (V$_{SS\_EXT}$ = 0V) to enable internal negative voltage generator.

2) Bypass mode: use V$_{SS\_EXT}$ (pin 20) to bypass and disable internal negative voltage generator.

3) The input 0.1 dB compression point is a linearity figure of merit. Refer to Table 2 for the operating RF input power (50Ω).

Switching Frequency

The PE43713 has a maximum 25 kHz switching rate in normal mode (pin 20 tied to ground). A faster switching rate is available in bypass mode (pin 20 tied to V_{SS_EXT}). The rate at which the PE43713 can be switched is then limited to the switching time as specified in **Table 3**.

Switching frequency is defined to be the speed at which the DSA can be toggled across attenuation states. Switching time is the time duration between the point the control signal reaches 50% of the final value and the point the output signal reaches within 10% or 90% of its target value.

Spur-free Performance

The typical spurious performance of the PE43713 in normal mode is –130 dBm (pin 20 tied to ground). If spur-free performance is desired, the internal negative voltage generator can be disabled by applying a negative voltage to V_{SS_EXT} (pin 20).

Glitch-less Attenuation State Transitions

The PE43713 features a novel architecture to provide the best-in-class glitch-less transition behavior when changing attenuation states. When RF input power is applied, the output power spikes are greatly reduced (≤0.3 dB) during attenuation state changes when comparing to previous generations of DSAs.

Truth Tables

Table 4–**Table 6** provide the truth tables for the PE43713.

Table 4 • *Parallel Truth Table*

Parallel Control Setting							Attenuation Setting RF1–RF2
D6	D5	D4	D3	D2	D1	D0	
L	L	L	L	L	L	L	Reference IL
L	L	L	L	L	L	H	0.25 dB
L	L	L	L	L	H	L	0.5 dB
L	L	L	L	H	L	L	1 dB
L	L	L	H	L	L	L	2 dB
L	L	H	L	L	L	L	4 dB

Table 4 • *Parallel Truth Table (Cont.)*

Parallel Control Setting							Attenuation Setting RF1–RF2
D6	D5	D4	D3	D2	D1	D0	
L	H	L	L	L	L	L	8 dB
H	L	L	L	L	L	L	16 dB
H	H	H	H	H	H	H	31.75 dB

Table 5 • *Serial Address Word Truth Table*

Address Word								Address Setting
A7 (MSB)	A6	A5	A4	A3	A2	A1	A0	
X	X	X	X	X	L	L	L	000
X	X	X	X	X	L	L	H	001
X	X	X	X	X	L	H	L	010
X	X	X	X	X	L	H	H	011
X	X	X	X	X	H	L	L	100
X	X	X	X	X	H	L	H	101
X	X	X	X	X	H	H	L	110
X	X	X	X	X	H	H	H	111

Table 6 • *Serial Attenuation Word Truth Table*

Attenuation Word								Attenuation Setting RF1–RF2
D7	D6	D5	D4	D3	D2	D1	D0 (LSB)	
L	L	L	L	L	L	L	L	Reference IL
L	L	L	L	L	L	L	H	0.25 dB
L	L	L	L	L	L	H	L	0.5 dB
L	L	L	L	L	H	L	L	1 dB
L	L	L	L	H	L	L	L	2 dB
L	L	L	H	L	L	L	L	4 dB
L	L	H	L	L	L	L	L	8 dB
L	H	L	L	L	L	L	L	16 dB
L	H	H	H	H	H	H	H	31.75 dB

Serial Addressable Register Map

Figure 2 provides the Serial Addressable register map for the PE43713.

Figure 2 • *Serial Addressable Register Map*

Bits can either be set to logic high or logic low

D7 must be set to logic low

MSB (last in)

LSB (first in)

Q15	Q14	Q13	Q12	Q11	Q10	Q9	Q8	Q7	Q6	Q5	Q4	Q3	Q2	Q1	Q0
A7	A6	A5	A4	A3	A2	A1	A0	D7	D6	D5	D4	D3	D2	D1	D0

Address Word   Attenuation Word
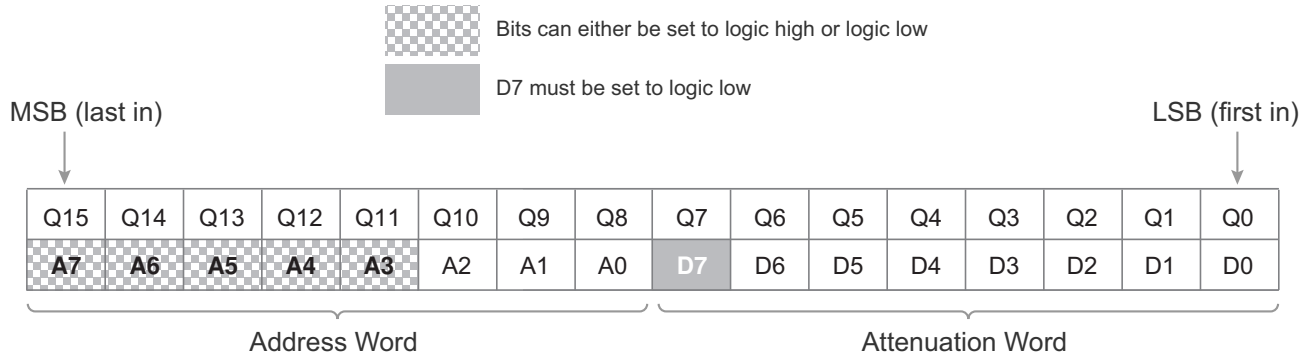
The attenuation word is derived directly from the value of the attenuation state. To find the attenuation word, multiply the value of the state by four, then convert to binary.

For example, to program the 18.25 dB state at address 3:

$$4 \times 18.25 = 73$$
$$73 \rightarrow 01001001$$

Address Word: XXXXX011
Attenuation Word: 01001001
Serial Input: XXXXX01101001001

Programming Options

Parallel/Serial Selection

Either a Parallel or Serial addressable interface can be used to control the PE43713. The $\overline{P}$/S bit provides this selection, with $\overline{P}$/S = LOW selecting the Parallel interface and $\overline{P}$/S = HIGH selecting the Serial interface.

Parallel Mode Interface

The Parallel interface consists of seven CMOS-compatible control lines that select the desired attenuation state, as shown in **Table 4**.

The Parallel interface timing requirements are defined by **Figure 4** (Parallel Interface Timing Diagram), **Table 9** (Parallel and Direct Interface AC Characteristics) and switching time (**Table 3**).

For Latched Parallel programming, the Latch Enable (LE) should be held LOW while changing attenuation state control values then pulse LE HIGH to LOW (per **Figure 4**) to latch new attenuation state into the device.

For Direct Parallel programming, the LE line should be pulled HIGH. Changing attenuation state control values will change device state to new attenuation. Direct mode is ideal for manual control of the device (using hardwire, switches, or jumpers).

Serial-Addressable Interface

The Serial-Addressable interface is a 16-bit Serial-In, Parallel-Out shift register buffered by a transparent latch. The 16-bits make up two words comprised of 8-bits each. The first word is the Attenuation Word, which controls the state of the DSA. The second word is the Address Word, which is compared to the static (or programmed) logical states of the A0, A1 and A2 digital inputs. If there is an address match, the DSA changes state; otherwise its current state will remain unchanged. **Figure 3** illustrates an example timing diagram for programming a state. It is required that all Parallel control inputs be grounded when the DSA is used in Serial-Addressable mode.

The Serial-Addressable interface is controlled using three CMOS-compatible signals: SI, Clock (CLK) and LE. The SI and CLK inputs allow data to be serially entered into the shift register. Serial data is clocked in LSB first.

The shift register must be loaded while LE is held LOW to prevent the attenuator value from changing as data is entered. The LE input should then be toggled HIGH and brought LOW again, latching the new data into the DSA. The Address Word truth table is listed in **Table 5**. The Attenuation Word truth table is listed in **Table 6**. A programming example of the serial register is illustrated in **Figure 2**. The serial timing diagram is illustrated in **Figure 3**.

Power-up Control Settings

The PE43713 will always initialize to the maximum attenuation setting (31.75 dB) on power-up for both the Serial Addressable and Latched Parallel modes of operation and will remain in this setting until the user latches in the next programming word. In Direct Parallel mode, the DSA can be preset to any state within the 31.75 dB range by pre-setting the Parallel control pins prior to power-up. In this mode, there is a 400 µs delay between the time the DSA is powered-up to the time the desired state is set. During this power-up delay, the device attenuates to the maximum attenuation setting (31.75 dB) before defaulting to the user defined state. If the control pins are left floating in this mode during power-up, the device will default to the minimum attenuation setting (insertion loss state).

Dynamic operation between Serial and Parallel programming modes is possible.

If the DSA powers up in Serial mode ($\overline{P}$/S = HIGH), all the Parallel control inputs DI[6:0] must be set to logic LOW. Prior to toggling to Parallel mode, the DSA must be programmed serially to ensure D[7] is set to logic LOW.

If the DSA powers up in either Latched or Direct Parallel mode, all Parallel pins DI[6:0] must be set to logic LOW prior to toggling to Serial Addressable mode ($\overline{P}$/S = HIGH), and held LOW until the DSA has been programmed serially to ensure bit D[7] is set to logic LOW.

The sequencing is only required once on power-up. Once completed, the DSA may be toggled between Serial and Parallel programming modes at will.
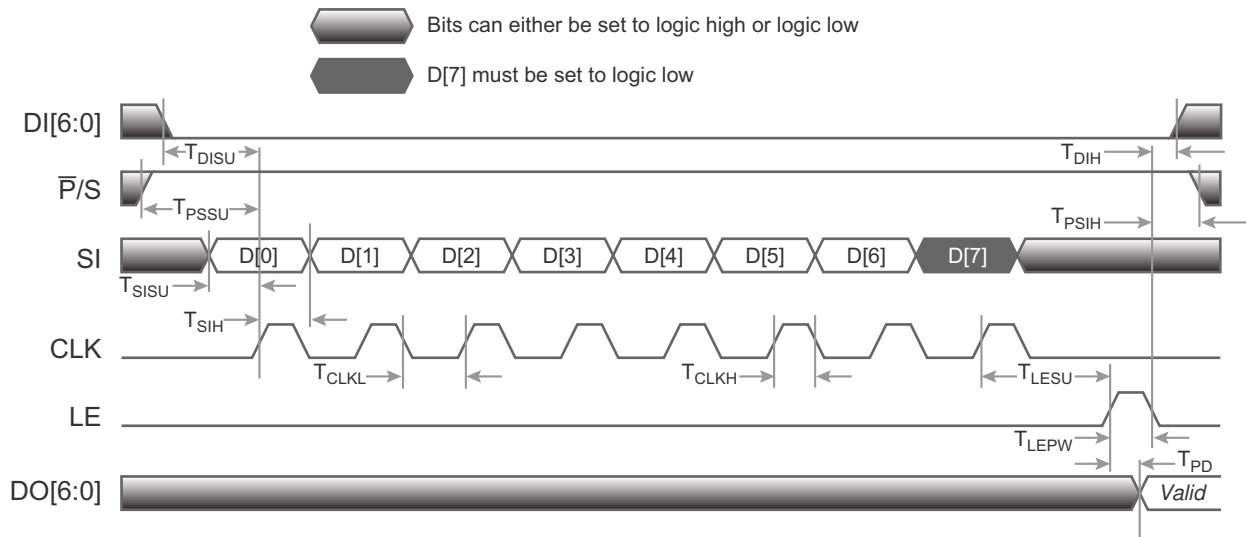
Figure 3 • *Serial Timing Diagram*

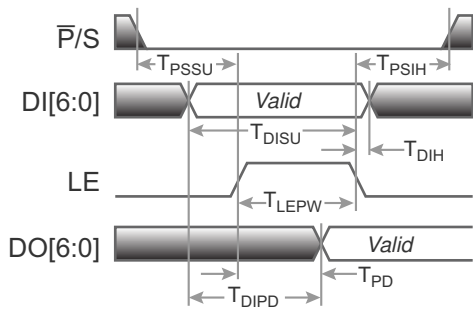## Figure 4 • *Latched Parallel/Direct Parallel Timing Diagram*

Table 7 • *Latch and Clock Specifications*

Latch Enable	Shift Clock	Function
0	↑	Shift register clocked
↑	X	Contents of shift register transferred to attenuator core

Table 8 • *Serial Interface AC Characteristics*[*]

Parameter/Condition	Min	Max	Unit
Serial clock frequency, F_{CLK}		10	MHz
Serial clock HIGH time, T_{CLKH}	30		ns
Serial clock LOW time, T_{CLKL}	30		ns
Last Serial clock rising edge setup time to Latch Enable rising edge, T_{LESU}	10		ns
Latch Enable minimum pulse width, T_{LEPW}	30		ns
Serial data setup time, T_{SISU}	10		ns
Serial data hold time, T_{SIH}	10		ns
Parallel data setup time, T_{DISU}	100		ns
Parallel data hold time, T_{DIH}	100		ns
Address setup time, T_{ASU}	100		ns
Address hold time, T_{AH}	100		ns
Parallel/Serial setup time, T_{PSSU}	100		ns
Parallel/Serial hold time, T_{PSIH}	100		ns
Digital register delay (internal), T_{PD}		10	ns
Note: * V_{DD} = 3.3V or 5.0V, –40 °C, < T_A < +105 °C, unless otherwise specified.			

Table 9 • *Parallel and Direct Interface AC Characteristics*[*]

Parameter/Condition	Min	Max	Unit
Latch Enable minimum pulse width, T_{LEPW}	30		ns
Parallel data setup time, T_{DISU}	100		ns
Parallel data hold time, T_{DIH}	100		ns
Parallel/Serial setup time, T_{PSSU}	100		ns
Parallel/Serial hold time, T_{PSIH}	100		ns
Digital register delay (internal), T_{PD}		10	ns
Digital register delay (internal, direct mode only), T_{DIPD}		5	ns
Note: * V_{DD} = 3.3V or 5.0V, –40 °C < T_A < +105 °C, unless otherwise specified.			

Figure 5 • *Power De-rating Curve, 9 kHz–6 GHz, –40 to +105 °C Ambient, 50Ω*
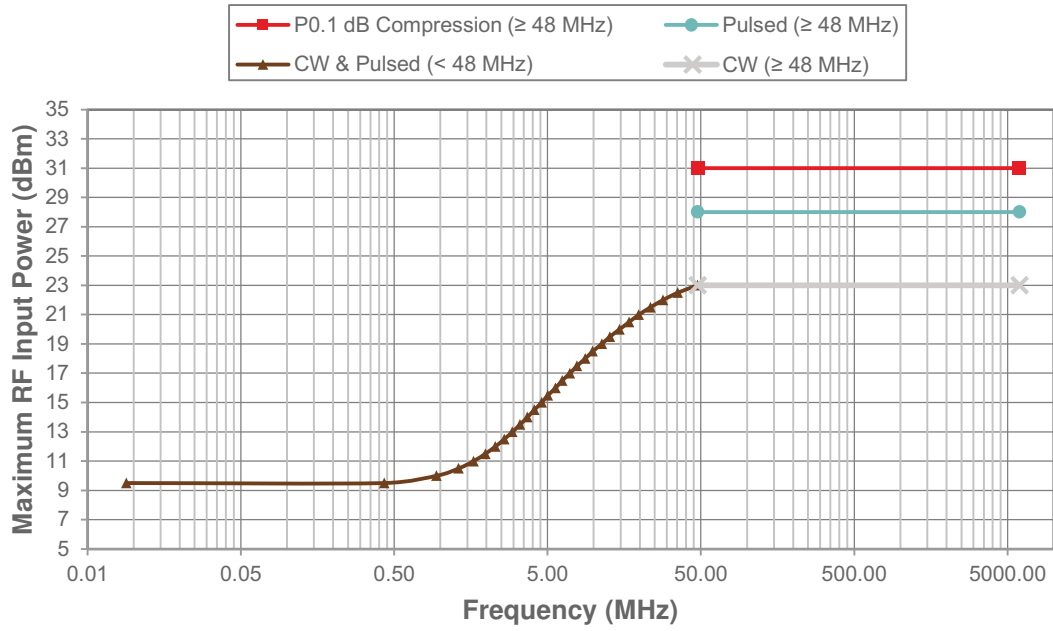
Typical Performance Data

Figure 6–**Figure 32** show the typical performance data at 25 °C and V_{DD} = 3.3V, RF1 = RF_{IN}, RF2 = RF_{OUT} (Z_S = Z_L = 50Ω) unless otherwise specified.

Figure 6 • *Insertion Loss vs Temperature*
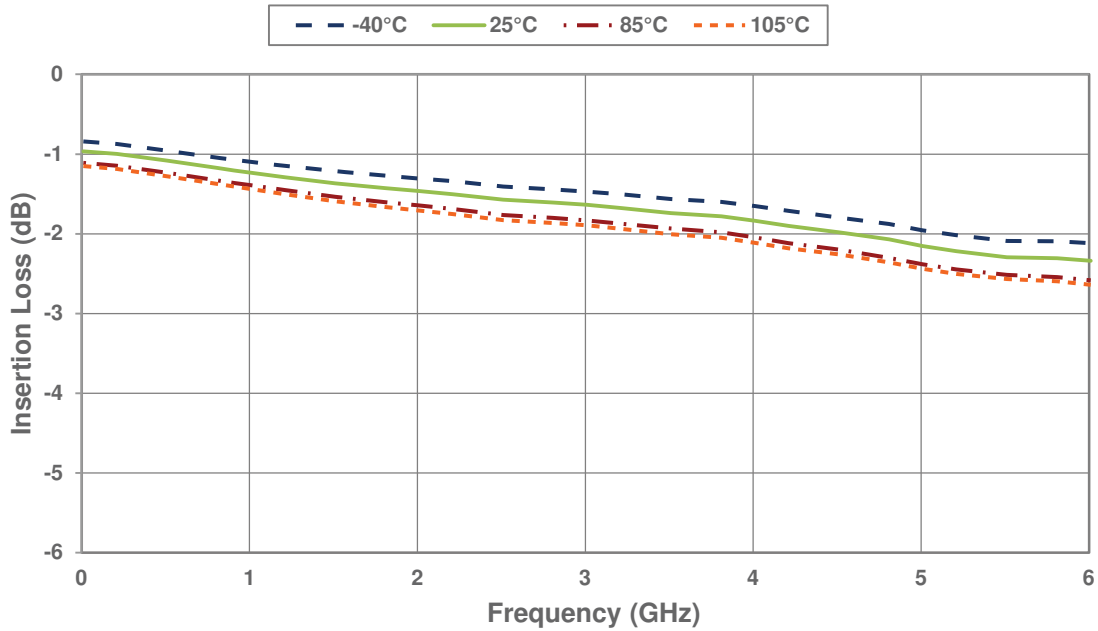
Figure 7 • *Input Return Loss vs Attenuation Setting*
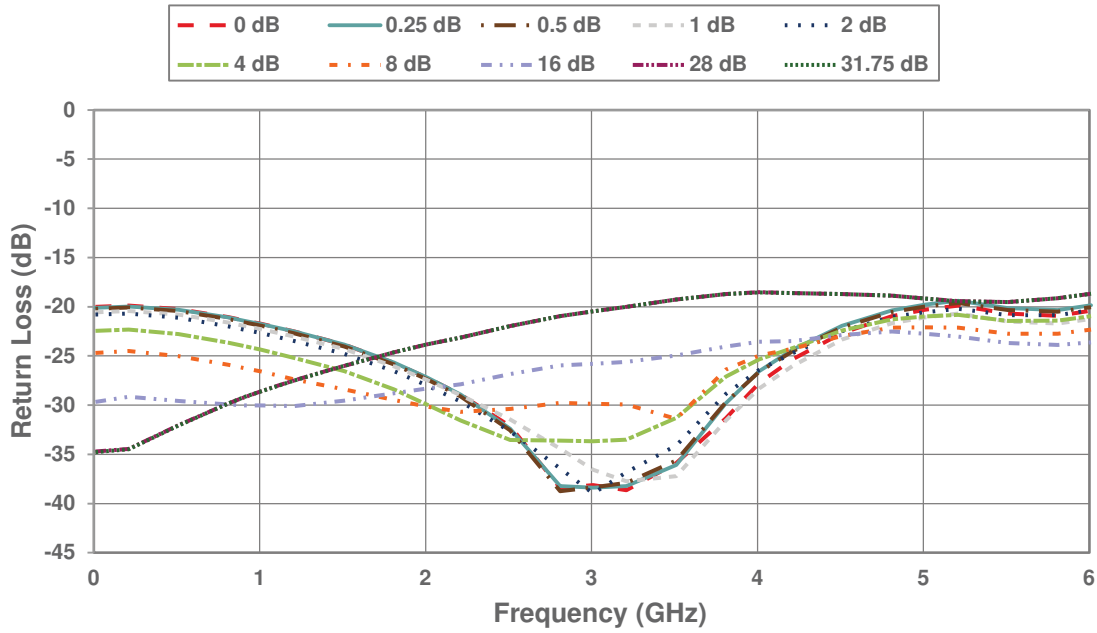
Figure 8 • *Output Return Loss vs Attenuation Setting*
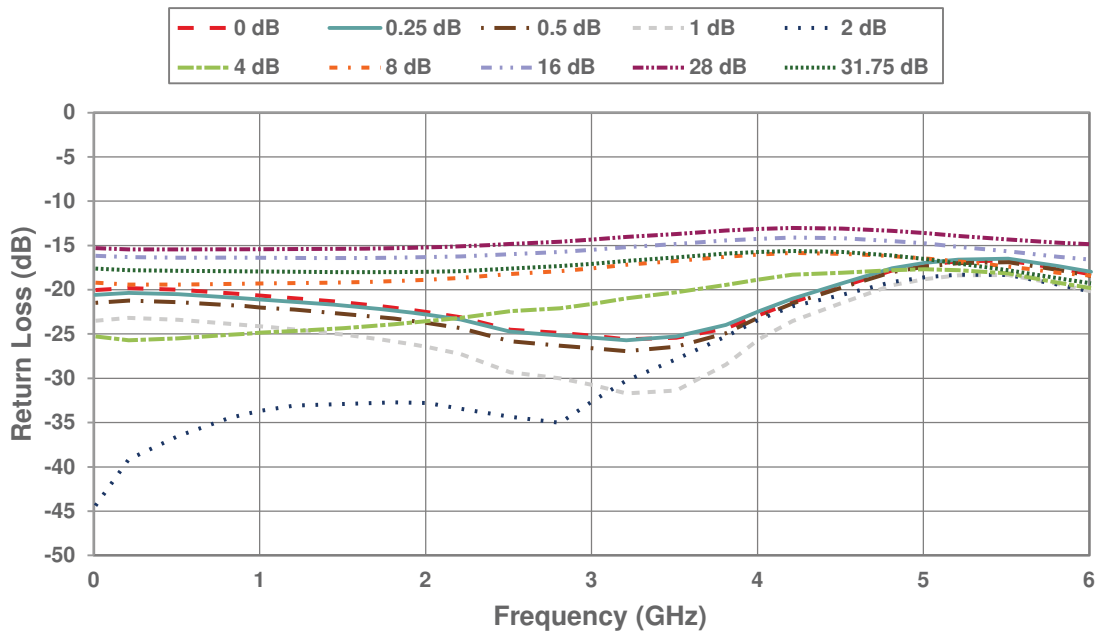
Figure 9 • *Input Return Loss for 16 dB Attenuation Setting vs Temperature*
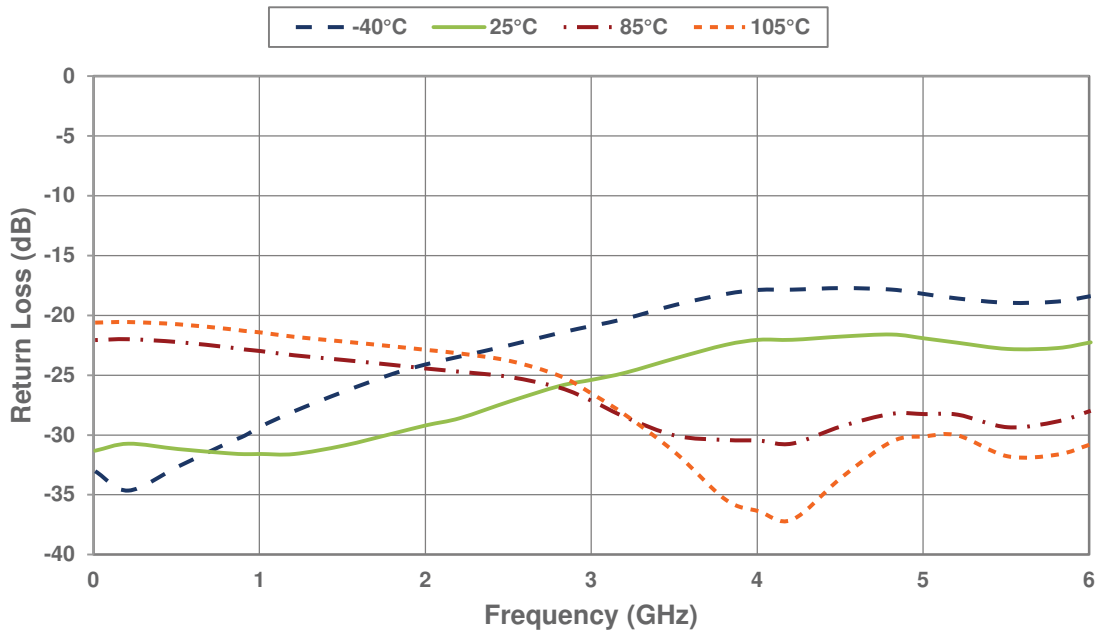
Figure 10 • *Output Return Loss for 16 dB Attenuation Setting vs Temperature*
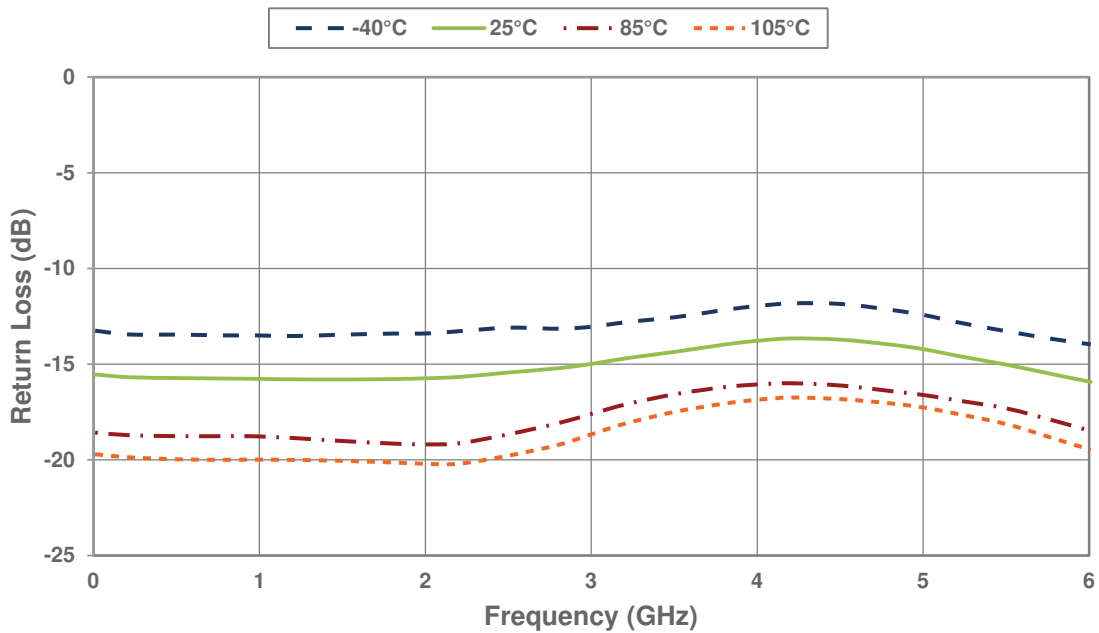
Figure 11 • *Relative Phase Error vs Attenuation Setting*
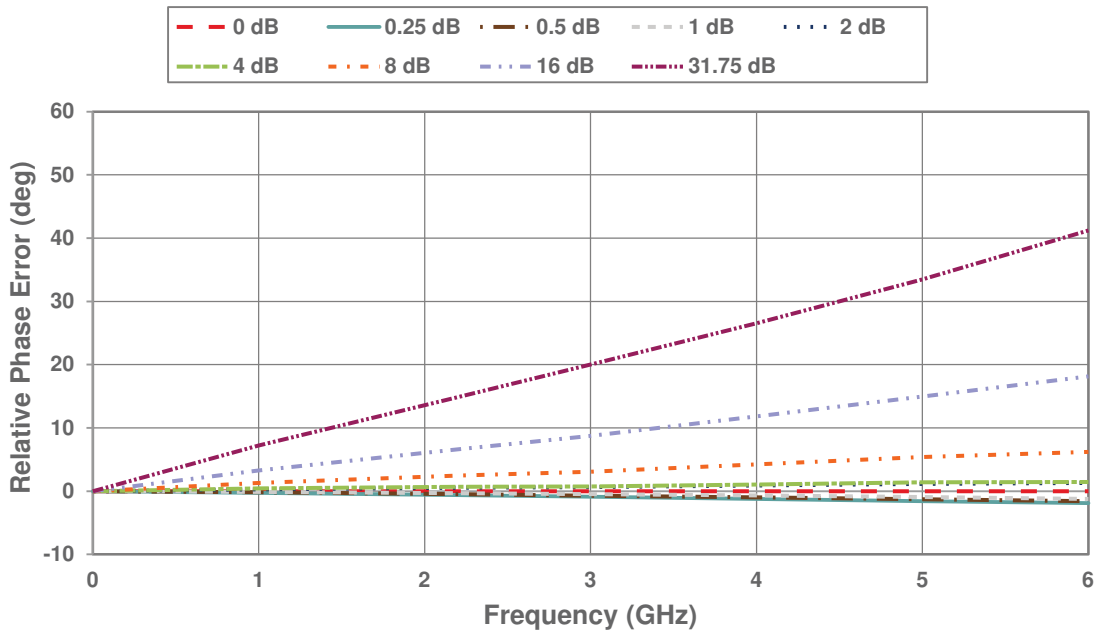
Figure 12 • *Relative Phase Error for 31.75 dB Attenuation Setting vs Frequency*
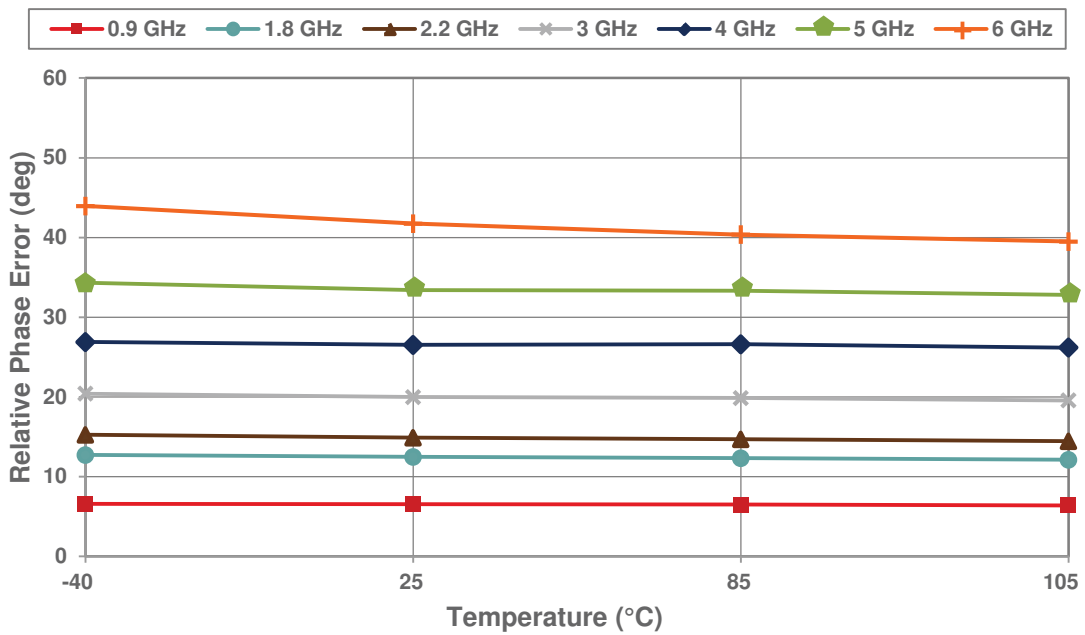
Figure 13 • *Attenuation Error @ 900 MHz vs Temperature*
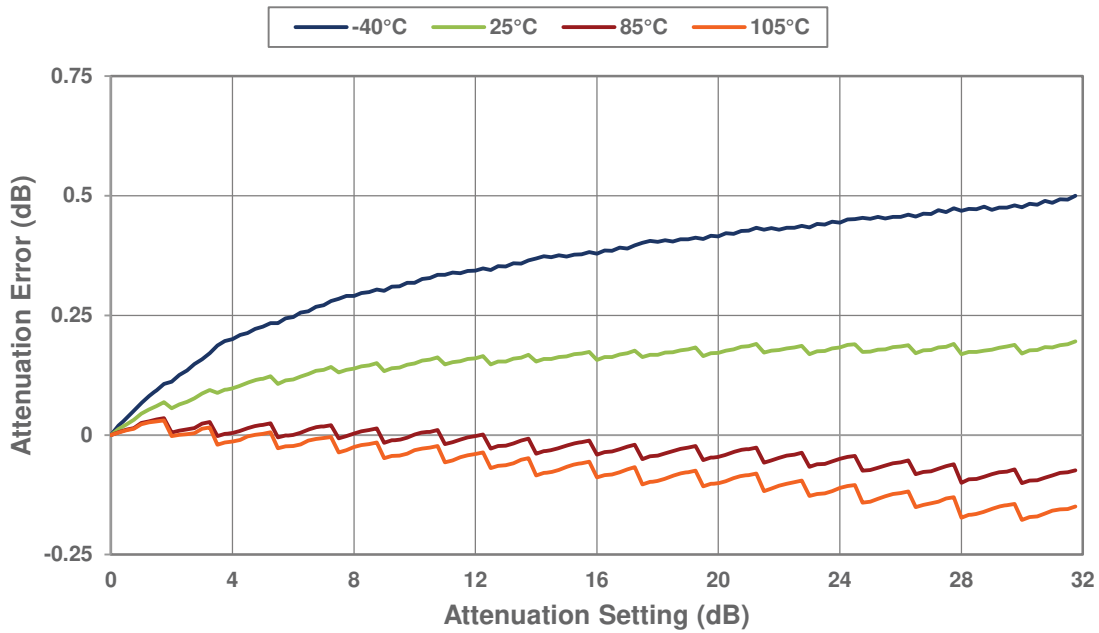
Figure 14 • *Attenuation Error @ 1800 MHz vs Temperature*
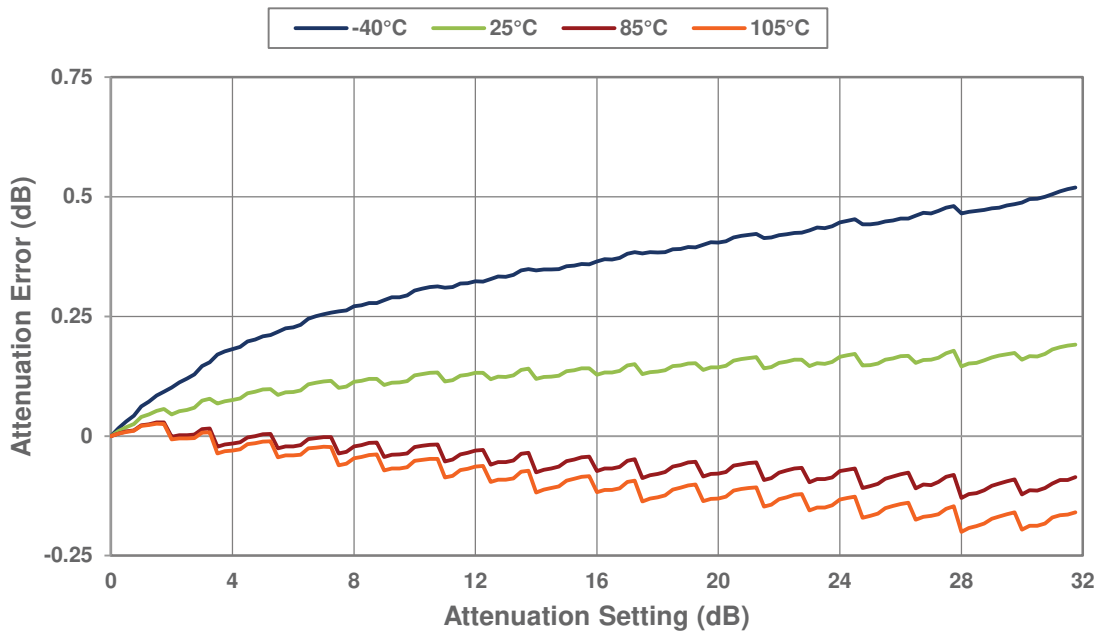
Figure 15 • *Attenuation Error @ 2200 MHz vs Temperature*
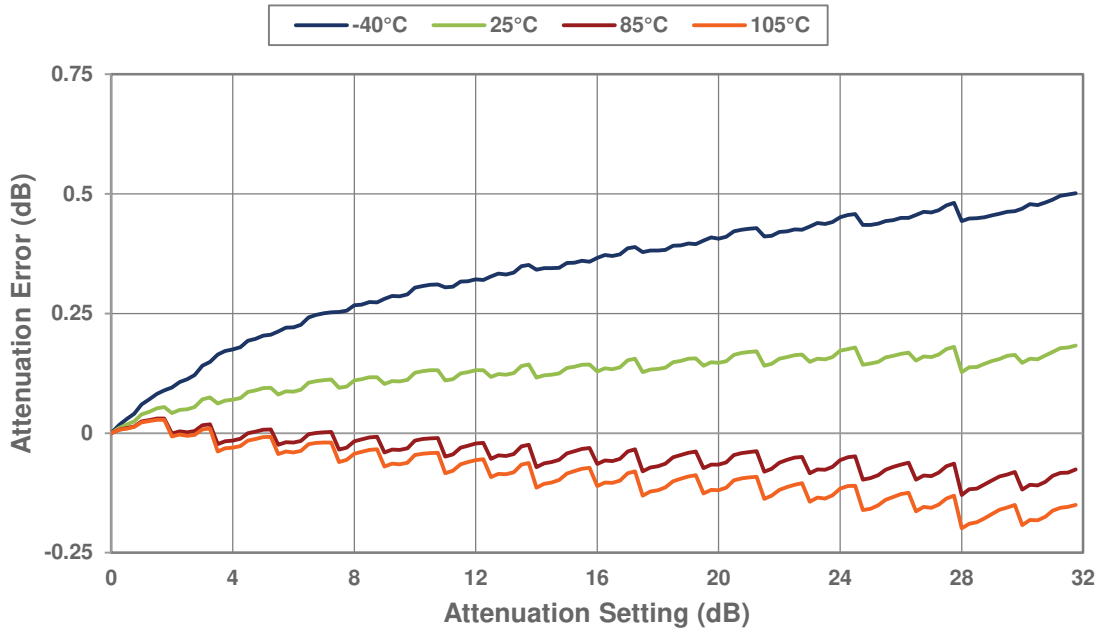
Figure 16 • *Attenuation Error @ 3000 MHz vs Temperature*
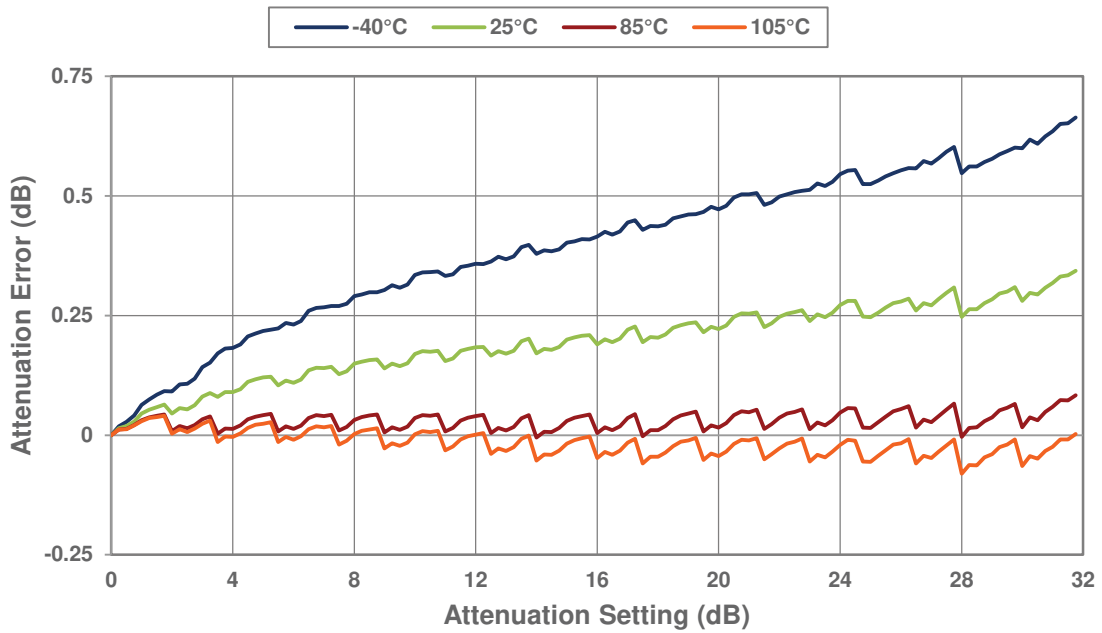
Figure 17 • *Attenuation Error @ 4000 MHz vs Temperature*
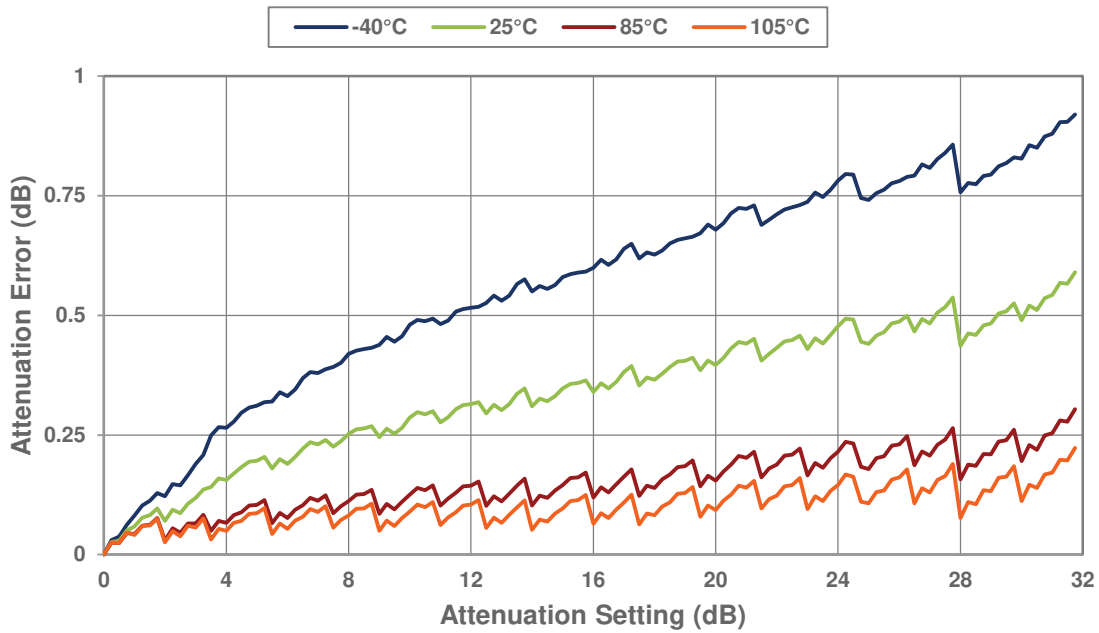
Figure 18 • *IIP3 vs Attenuation Setting*
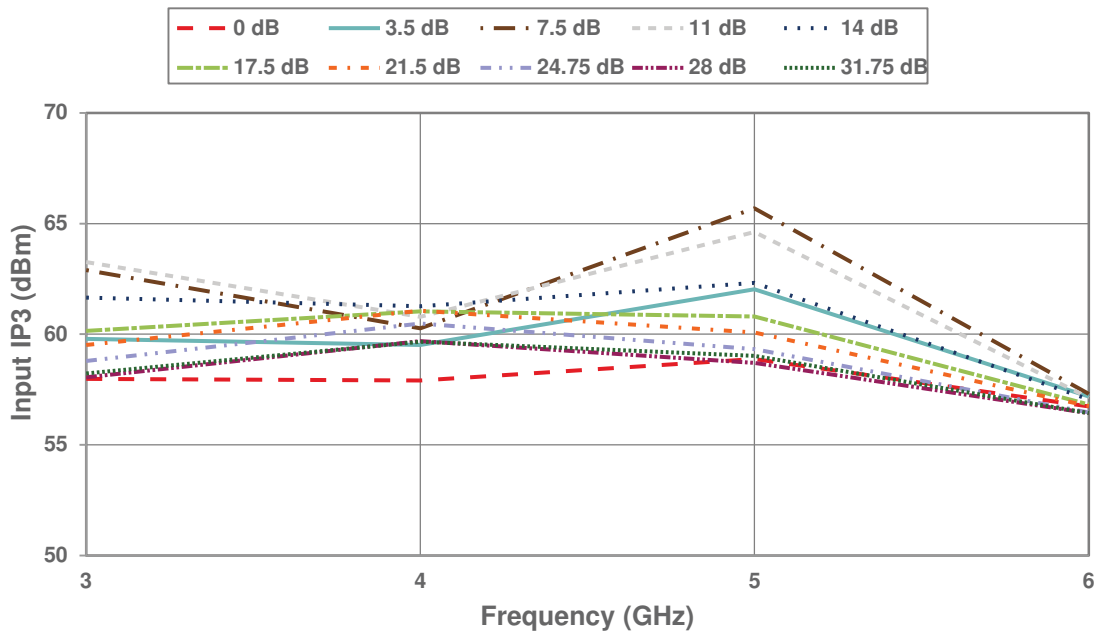
Figure 19 • *0.25 dB Step Attenuation vs Frequency*(*)
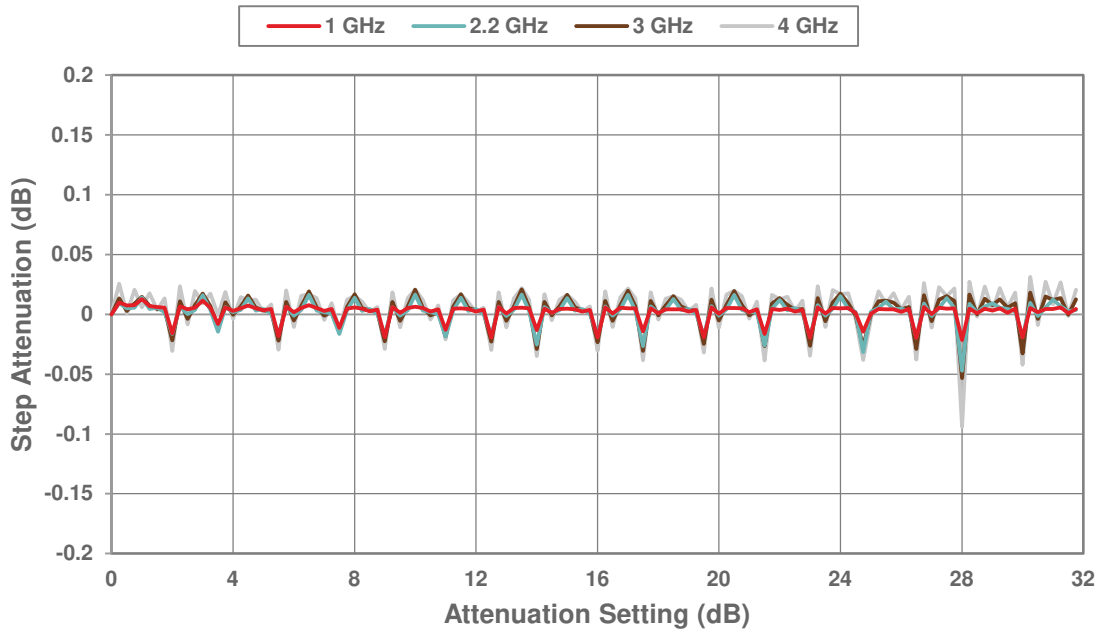
Note: * Monotonicity is held so long as step attenuation does not cross below –0.25 dB.

Figure 20 • *0.25 dB Step, Actual vs Frequency*
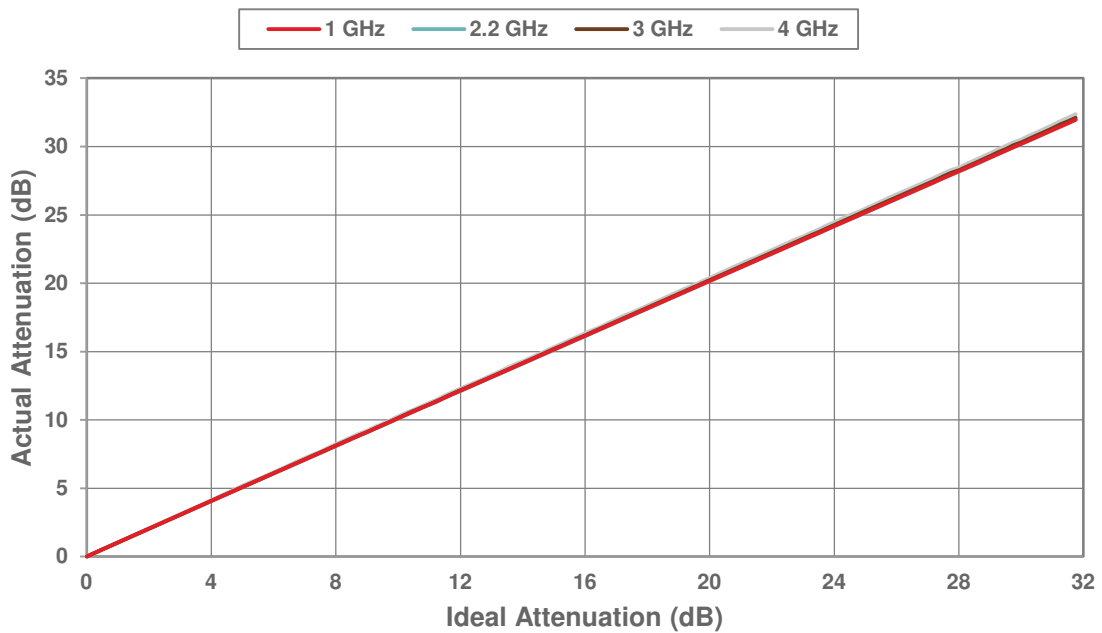
Figure 21 • *0.25 dB Major State Bit Error vs Attenuation Setting*
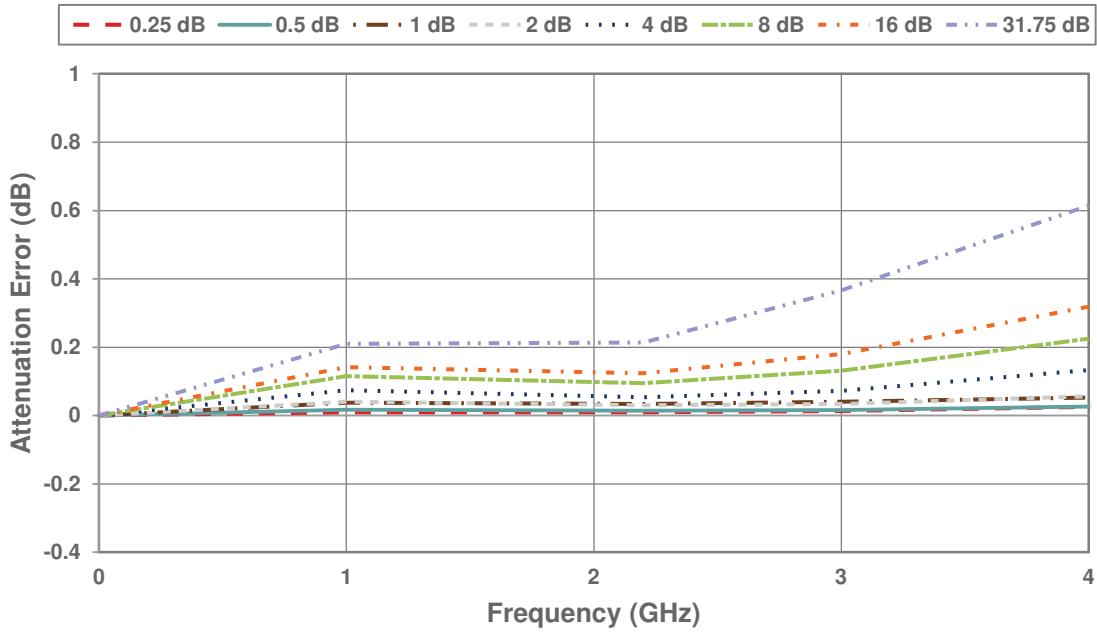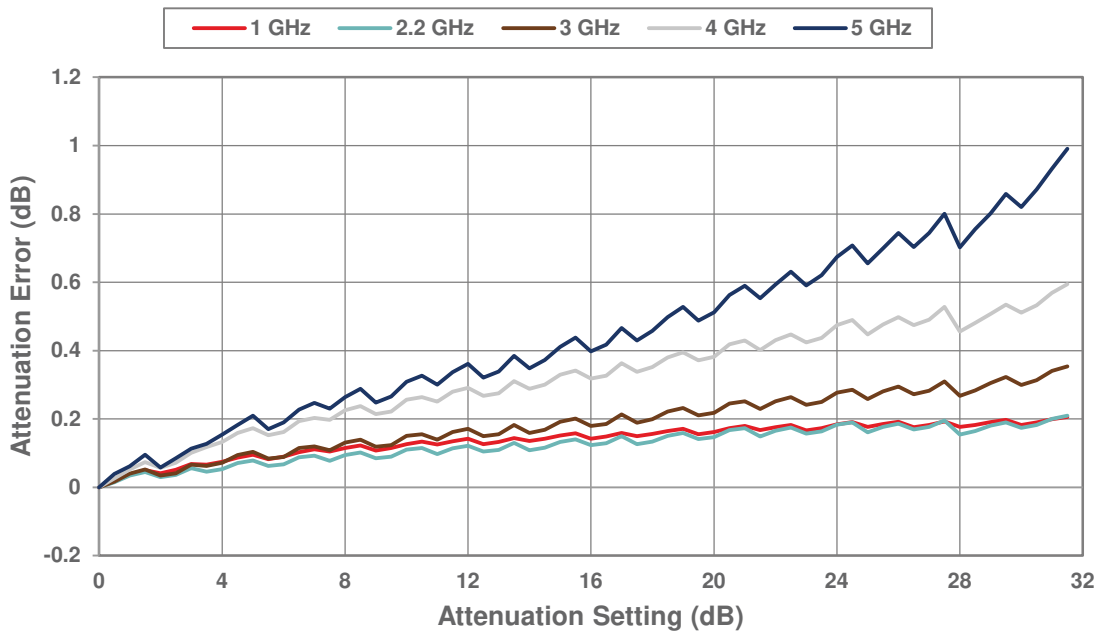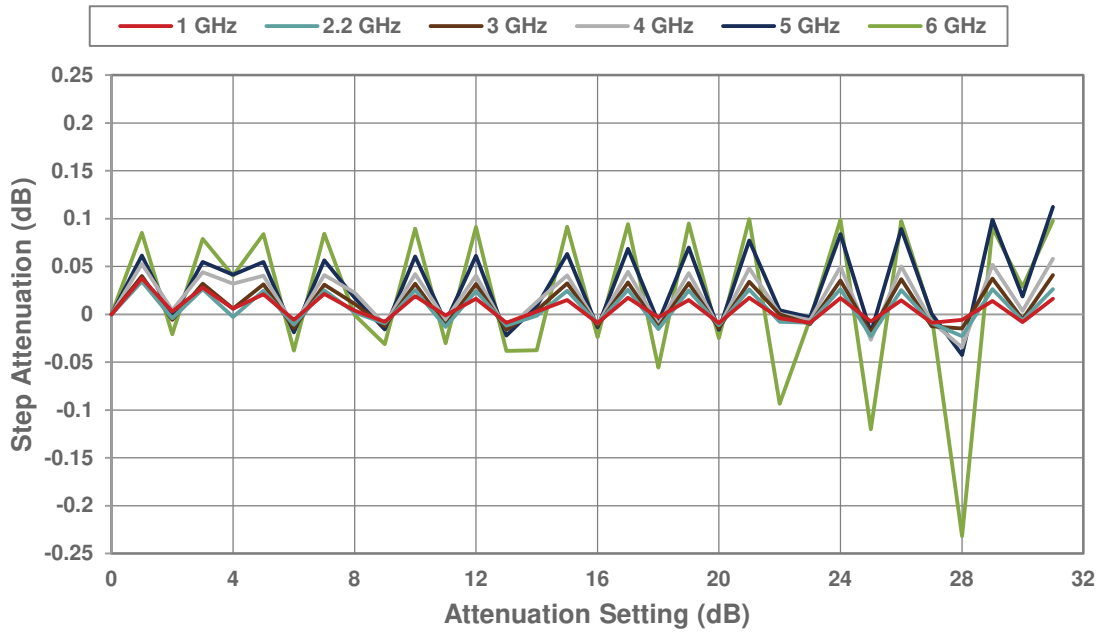

Figure 22 • *0.25 dB Attenuation Error vs Frequency*
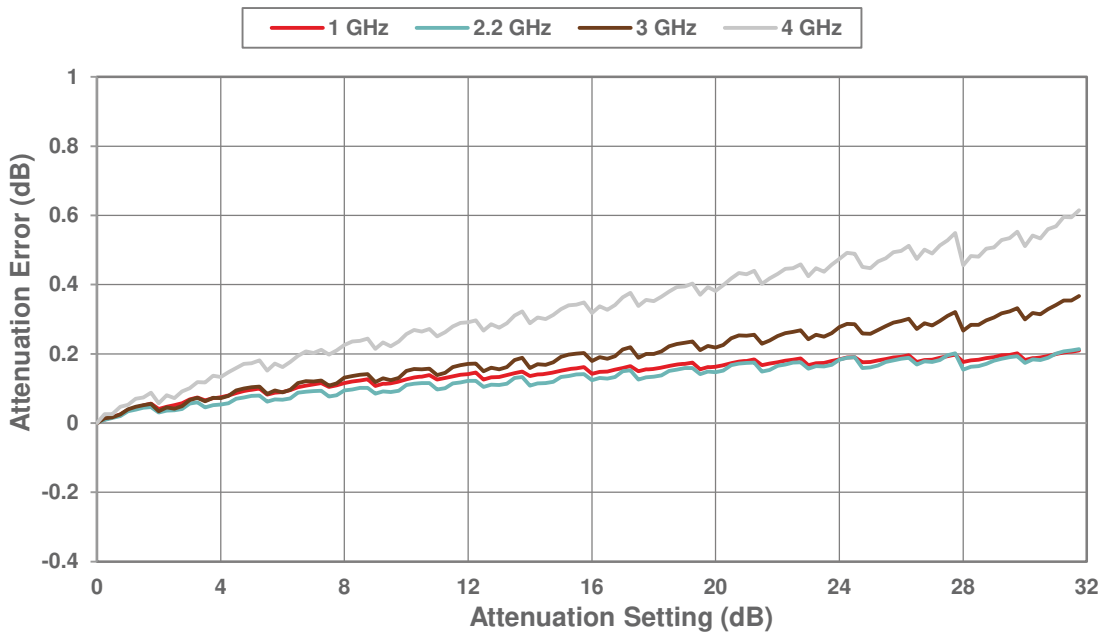
Figure 23 • *0.5 dB Step Attenuation vs Frequency*(*)
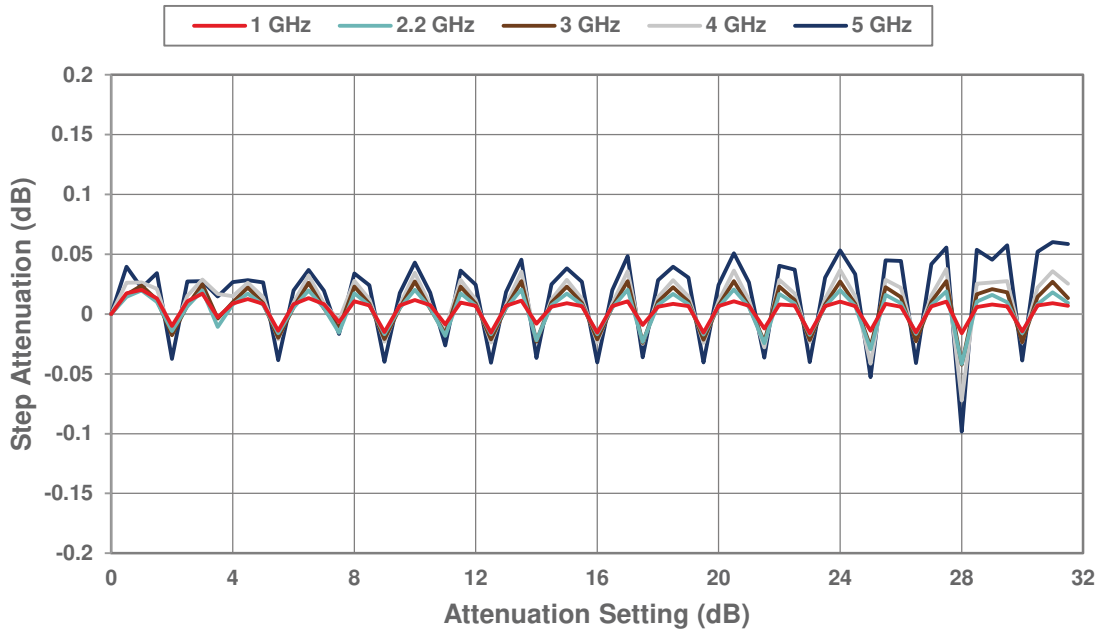
Note: * Monotonicity is held so long as step attenuation does not cross below –0.5 dB.

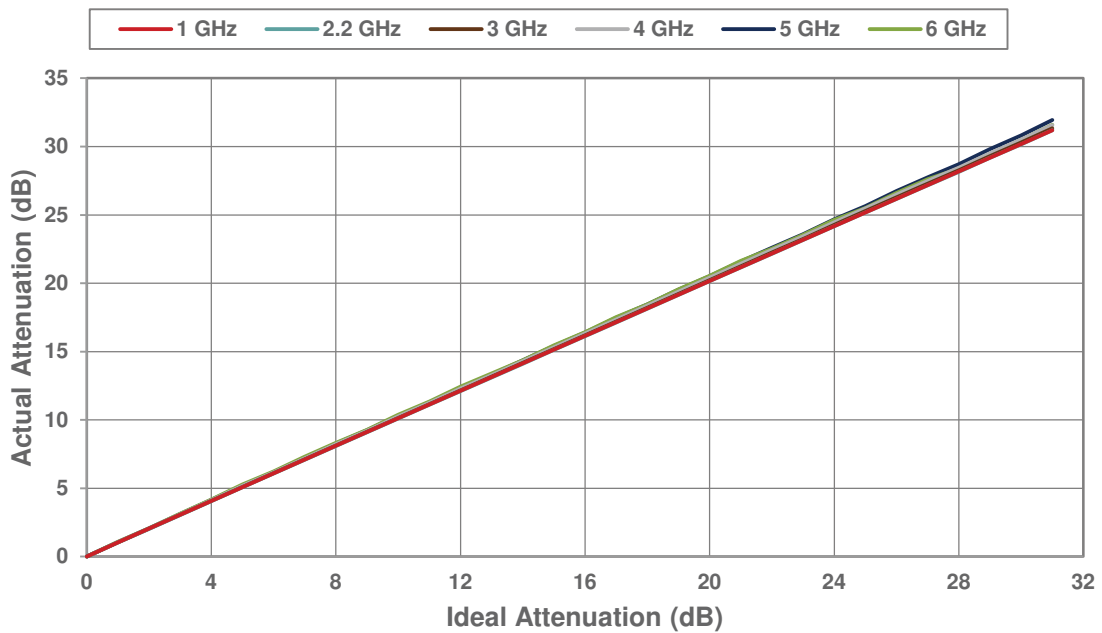**Figure 24 • *0.5 dB Step, Actual vs Frequency***
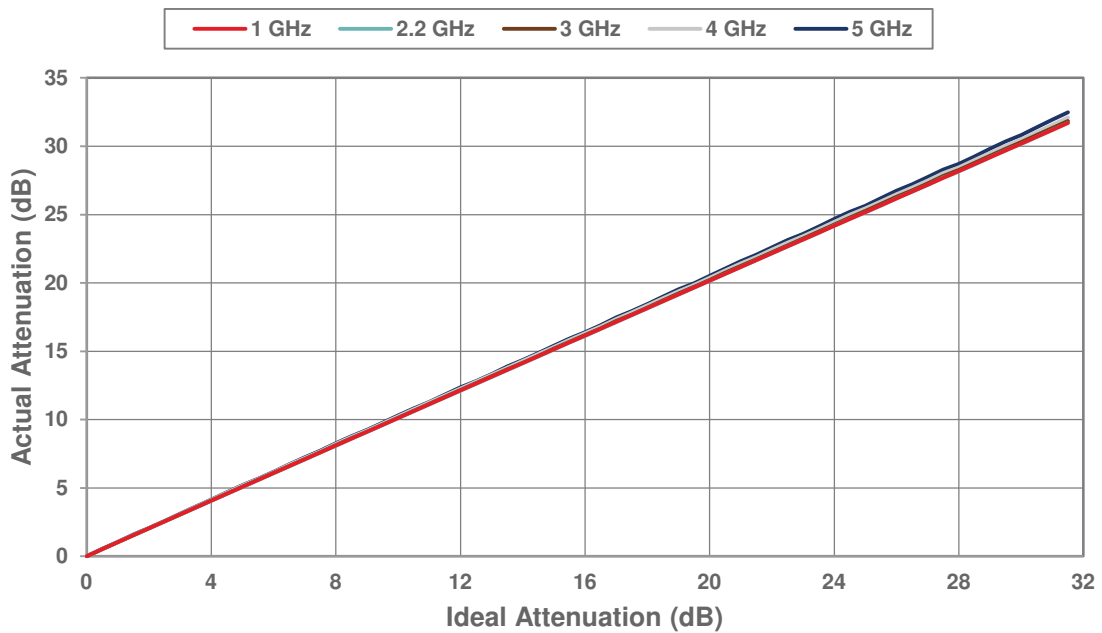
Figure 25 • *0.5 dB Major State Bit Error vs Attenuation Setting*
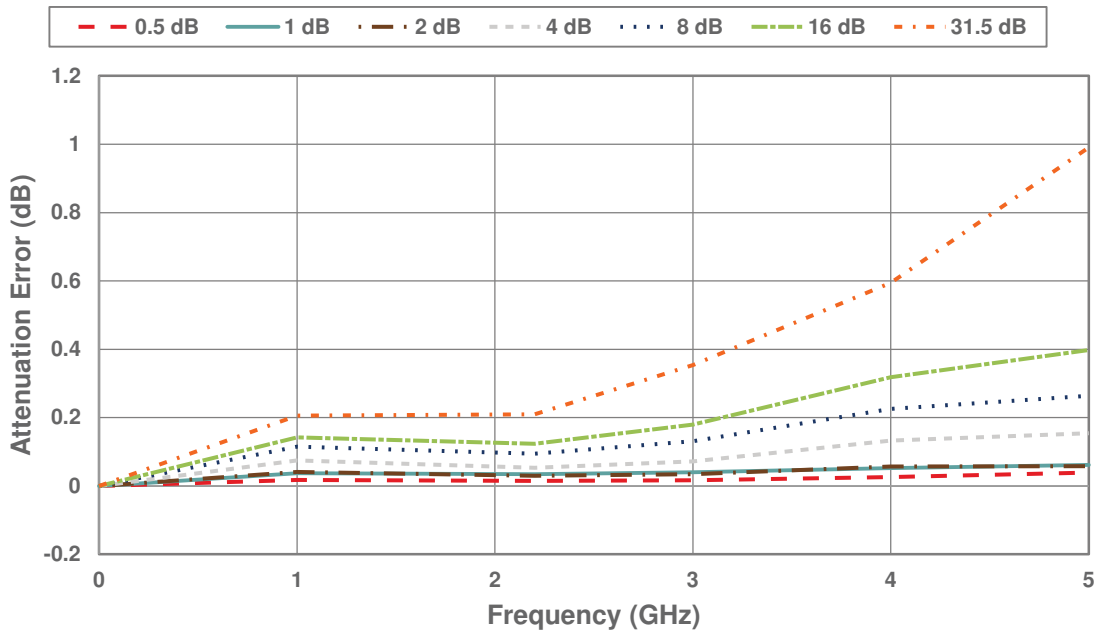
Figure 26 • *0.5 dB Attenuation Error vs Frequency*

Figure 27 • 1 dB Step Attenuation vs Frequency[*]

Note: *   Monotonicity is held so long as step attenuation does not cross below –1 dB.

Figure 28 • 1 dB Step, Actual vs Frequency
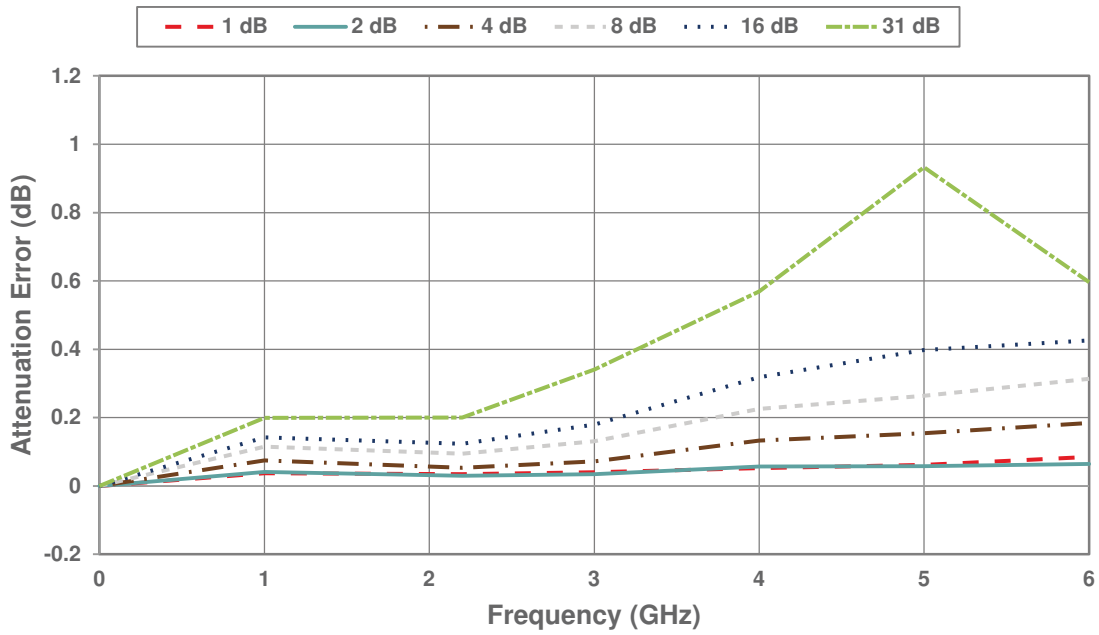
Figure 29 • *1 dB Major State Bit Error vs Attenuation Setting*

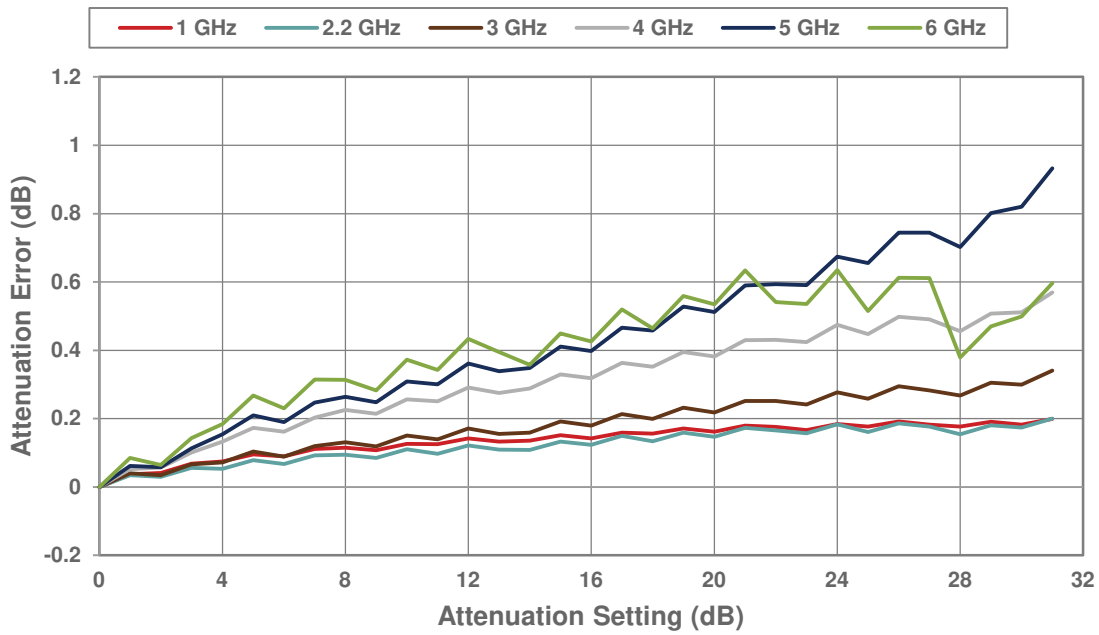**Figure 30 • *1 dB Attenuation Error vs Frequency***

Figure 31 • Attenuation Transient (15.75–16 dB), Typical Switching Time = 275 ns
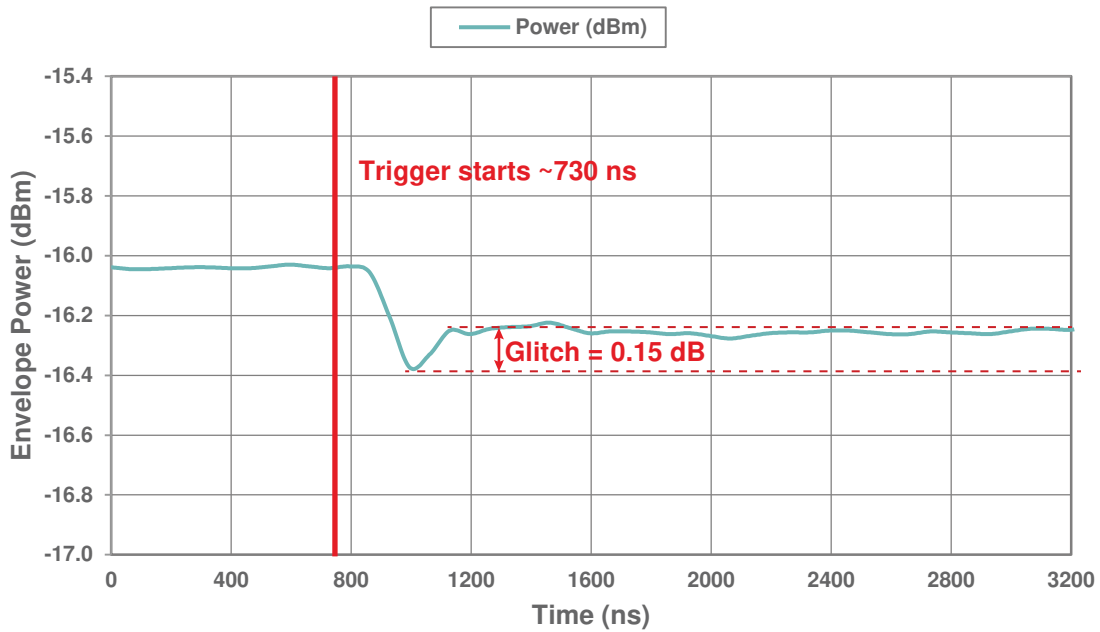

Figure 32 • Attenuation Transient (16–15.75 dB), Typical Switching Time = 275 ns